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STC08DE150HP

Hybrid emitter switched bipolar transistor ESBT[®] 1500 V - 8 A - 0.075 Ω

Features

V _{CS(ON)}	Ι _C	R _{CS(ON)}
0.6 V	8 A	0.075 Ω

- Low equivalent ON resistance
- Very fast-switching: up to 150 kHz
- Squared RBSOA: up to 1500 V
- Very low C_{ISS} driven by $R_G = 47 \Omega$

Application

 Single switch SMPS based on three-phase mains

Description

The STC08DE150HP is manufactured in a hybrid structure, using dedicated high voltage bipolar and low voltage MOSES1 technologies, aimed at providing the best proformance in an ESBT topology.

The STC0 3DE150HP is designed for use in auxiliary flyback SMPS for any three-phase apolication.

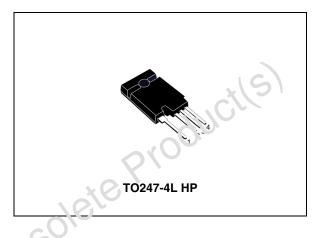


Figure 1. Internal schematic diagrams

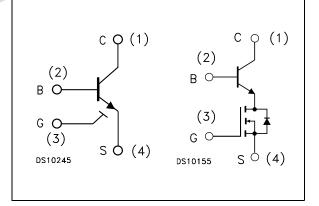


Table 1. Device summary

Order code	Marking	Package	Packing
STC08DE150HP	C08DE150HP	TO247-4L HP	Tube

Electrical ratings 1

Table 2.	Absolute maximu	m ratings

Symbol	Parameter	Value	Unit		
V _{CS(SS)}	Collector-source voltage ($V_{BS} = V_{GS} = 0$)	1500	V		
V _{BS(OS)}	Base-source voltage ($I_C = 0$, $V_{GS} = 0$)	30	V		
V _{SB(OS)}	Source-base voltage ($I_C = 0$, $V_{GS} = 0$)	9	V		
V _{GS}	Gate-source voltage	±20	v		
Ι _C	Collector current	8	A		
I _{CM}	Collector peak current (t _P < 5 ms)	15	А		
Ι _Β	Base current	8	А		
I _{BM}	Base peak current (t _P < 1 ms)	15	А		
P _{tot}	Total dissipation at $T_c \le 25 \text{ °C}$		W		
T _{stg}	Storage temperature -40 to 150		°C		
Τ _J	Max. operating junction temperature 125				
	0/02				
Table 3.	Thermal data	1			
		1			

Table 3. Thermal data

	Symbol	S Parameter	Value	Unit
	R _{thJC}	Thermal resistance junction-case	2.4	°C/W
	te P	rodu		
01050.				

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

 Table 4.
 Electrical characteristics

			· · · · · · · ·				
	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	I _{CS(SS)}	Collector cut-off current $(V_{BS} = V_{GS} = 0)$	V _{CS} = 1500 V			100	μA
	I _{BS(OS)}	Base cut-off current ($I_C = 0, V_{GS} = 0$)	V _{BS} = 30 V			10	μA
	I _{SB(OS)}	Source cut-off current $(I_{C} = 0, V_{GS} = 0)$	V _{SB} = 9 V			:00	μA
	I _{GS(OS)}	Gate-source leakage current (V _{BS} = 0)	V _{GS} = ± 20 V	0		500	nA
	V _{CS(ON)}	Collector-source ON voltage			0.6 0.6	1.4	V V
	h _{FE} ⁽¹⁾	DC current gain	$I_{C} = 8 A$ $V_{CS} = 1 \sqrt{V_{GS}} = 10 V$ $I_{C} = 5 A$ $V_{CS} = 1 V$ $V_{GS} = 10 V$	4.5 8	7.5 10		
	V _{BS(ON)}	Base-source ON voltage	V_{G} ; = 10 V I_{C} = 8 A I_{B} = 1.6 A V_{GS} - 10 V I_{C} = 5 A I_{B} = 0.5 A		1.5 1	2	V V
	V _{GS(th)}	Gate threshold voltage	V _{BS} = V _{GS} I _B = 250 μA	1.5	2.2	3	V
obsole	C _{iss}	Input capacitar ct $(V_{GS} = V_{C,3} = f)$	V _{CS} = 25 V f = 1 MHz		750		pF
	Q _{GS(tot)}	Gate-scince charge (\' _{CF} = 0)	$V_{GS} = 10 V I_{C} = 8 A V_{CS} = 25 V$		12.5		nC
		Inductive load Storage time Fall time	$\label{eq:VGS} \begin{array}{ll} V_{GS} = 10 \ V & R_G = 47 \ \Omega \\ V_{Clamp} = 1200 \ V & t_p = 4 \ \mu s \\ I_C = 5 \ A & I_B = 0.5 \ A \end{array}$		526 8.5		ns ns
	t _s t _f	Inductive load Storage time Fall time	$\label{eq:VGS} \begin{array}{ll} V_{GS} = 10 \ V & R_G = 47 \ \Omega \\ V_{Clamp} = 1200 \ V & t_p = 4 \ \mu s \\ I_C = 5 \ A & I_B = 1 \ A \end{array}$		884 16		ns ns
	V _{CSW}	Maximum collector- source voltage at turn- off without snubber	$R_{G} = 47 \Omega$ $h_{FE} = 5 I_{C} = 8 A$	1500			V
	V _{CS(dyn)}	Collector-source dynamic voltage (0.5 µs)	$\begin{split} & V_{\text{CC}} = V_{\text{Clamp}} = 300 \; V \\ & V_{\text{GS}} = 10 \; V & I_{\text{C}} = 4 \; A \\ & I_{\text{B}} = 0.8 \; A & t_{\text{peak}} = 500 \; \text{ns} \\ & R_{\text{G}} = 47 \; \Omega & I_{\text{Bpeak}} = 8 \; A \; (2I_{\text{C}}) \end{split}$		6		V
	V _{CS(dyn)}	Collector-source dynamic voltage (1 µs)	$\begin{split} & V_{\text{CC}} = V_{\text{Clamp}} = 300 \; V \\ & V_{\text{GS}} = 10 \; V & I_{\text{C}} = 4 \; A \\ & I_{\text{B}} = 0.8 \; A & t_{\text{peak}} = 500 \; \text{ns} \\ & R_{\text{G}} = 47 \; \Omega & I_{\text{Bpeak}} = 8 \; A \; (2I_{\text{C}}) \end{split}$		2.2		V

1. Pulsed duration = 300 $\mu s,$ duty cycle $\leq 1.5\%.$



2.1 Electrical characteristics (curves)





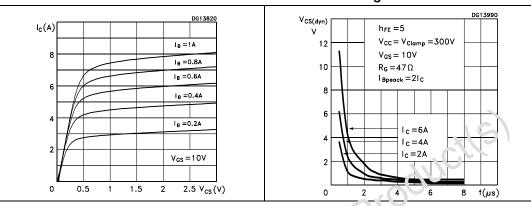
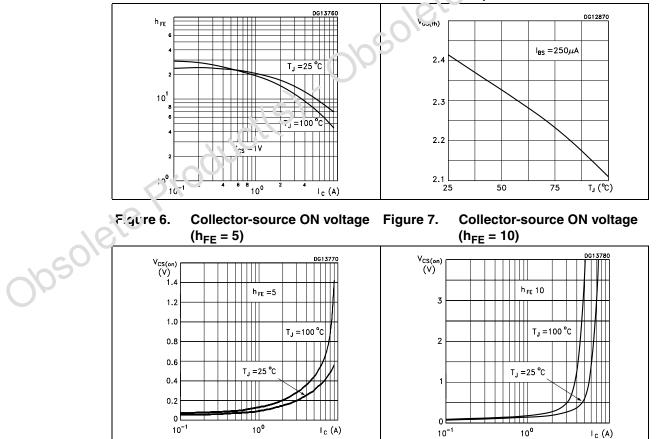
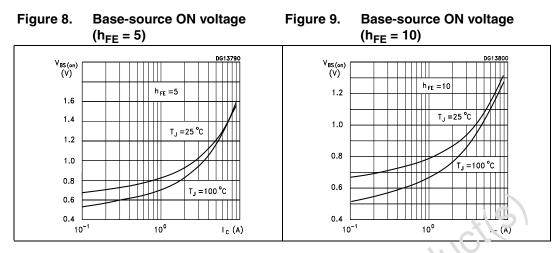
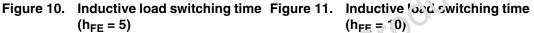




Figure 5. Gate threshold voltage vs. temperature







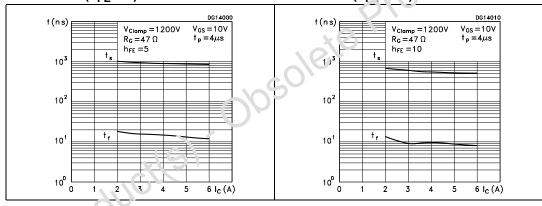
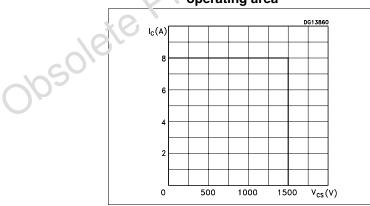


Figure 12. Reverse biased safe operating area



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

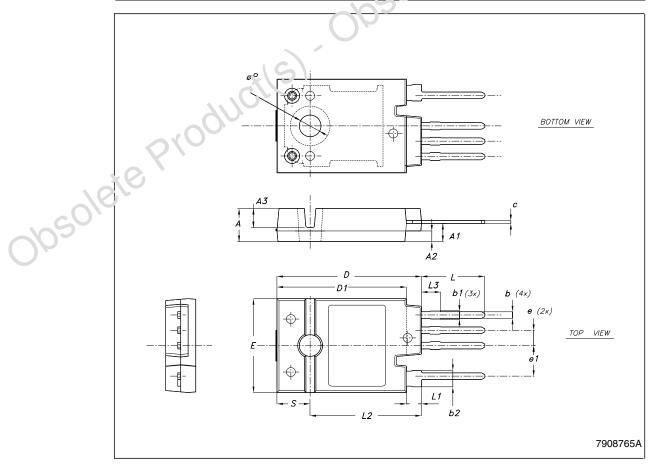


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obsolete Product(s). Obsolete Product(s)

TO247-4L	HP	mechanical	data
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DIM.		mm.	
	MIN.	ТҮР	MAX.
A	5.50	5.65	5.80
A1	2.85	3.15	3.25
A2		1.92	
A3		3.18	
b	0.95	1.10	1.30
b1	1.10		1.50
b2	2.50		2.90
С	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15./5
е		2.54	-07-
e1		5.08	
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	





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4 Revision history

Table 5.Document revision history

	Date	Revision	Changes
	26-Oct-2006	1	First release.
	15-Jun-2009	2	Document status promoted from preliminary data to datasheet.
obsole	tepro	Jucit	obsolete Productis



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